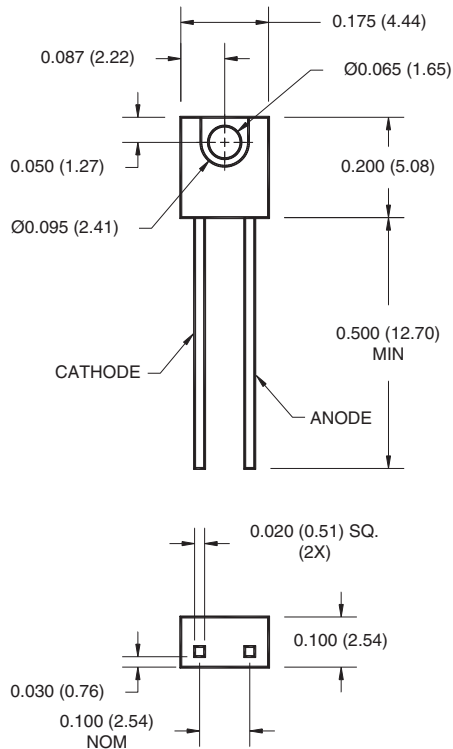




**THE DATASHEET OF
QEE113E3R0**

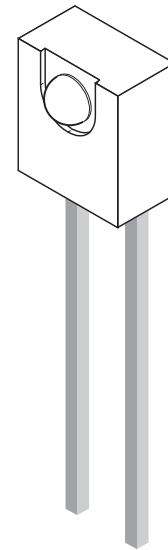


PACKAGE DIMENSIONS

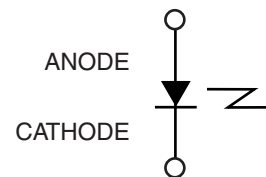


NOTES:

1. Dimensions for all drawings are in inches (mm).
2. Tolerance of $\pm .010$ (.25) on all non-nominal dimensions unless otherwise specified.



SCHEMATIC



DESCRIPTION

The QEE113 is a 940 nm GaAs LED encapsulated in a medium wide angle, plastic sidelooker package.

FEATURES

- $\lambda = 940$ nm
- Package Type = Sidelooker
- Chip Material = GaAs
- Matched Photosensor: QSE113
- Medium Wide Emission Angle, 50°
- Package Material: Clear Epoxy
- High Output Power
- Gray stripe on the top side

ABSOLUTE MAXIMUM RATINGS ($T_A = 25^\circ\text{C}$ unless otherwise specified)

Parameter	Symbol	Rating	Unit
Operating Temperature	T_{OPR}	-40 to +100	$^\circ\text{C}$
Storage Temperature	T_{STG}	-40 to +100	$^\circ\text{C}$
Soldering Temperature (Iron) ^(2,3,4)	T_{SOL-I}	240 for 5 sec	$^\circ\text{C}$
Soldering Temperature (Flow) ^(2,3)	T_{SOL-F}	260 for 10 sec	$^\circ\text{C}$
Continuous Forward Current	I_F	50	mA
Reverse Voltage	V_R	5	V
Power Dissipation ⁽¹⁾	P_D	100	mW

NOTES:

1. Derate power dissipation linearly 1.33 mW/ $^\circ\text{C}$ above 25 $^\circ\text{C}$.
2. RMA flux is recommended.
3. Methanol or isopropyl alcohols are recommended as cleaning agents.
4. Soldering iron 1/16" (1.6 mm) minimum from housing.

ELECTRICAL / OPTICAL CHARACTERISTICS ($T_A = 25^\circ\text{C}$)

Parameter	Test Conditions	Symbol	Min	Typ	Max	Units
Peak Emission Wavelength	$I_F = 100\text{ mA}$	λ_{PE}	—	940	—	nm
Emission Angle	$I_F = 100\text{ mA}$	$2\theta_{1/2}$	—	50	—	Deg.
Forward Voltage	$I_F = 100\text{ mA}$, $t_p = 20\text{ ms}$	V_F	—	—	1.5	V
Reverse Current	$V_R = 5\text{ V}$	I_R	—	—	10	μA
Radiant Intensity	$I_F = 100\text{ mA}$, $t_p = 20\text{ ms}$	I_E	3	—	12	mW/sr
Rise Time	$I_F = 100\text{ mA}$	t_r	—	1000	—	ns
Fall Time		t_f	—	1000	—	ns

Fig.1 Normalized Radiant Intensity vs. Forward Current

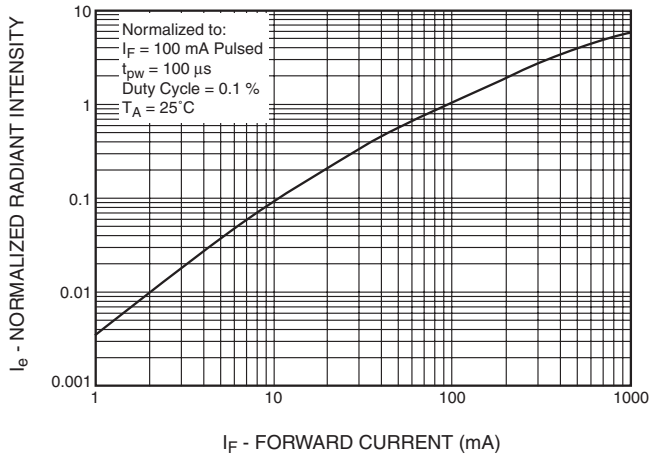


Fig.2 Coupling Characteristics of QEE113 And QSE113

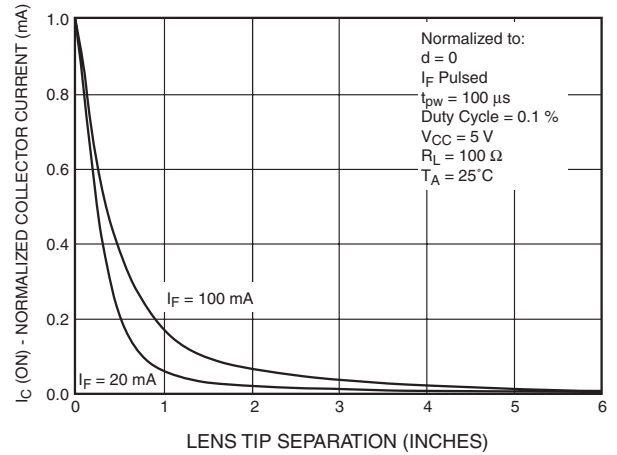


Fig.3 Forward Voltage vs. Ambient Temperature

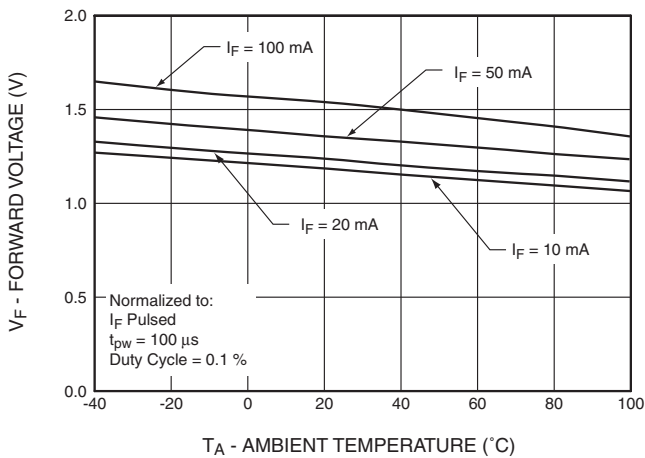


Fig. 4 Normalized Intensity vs. Wavelength

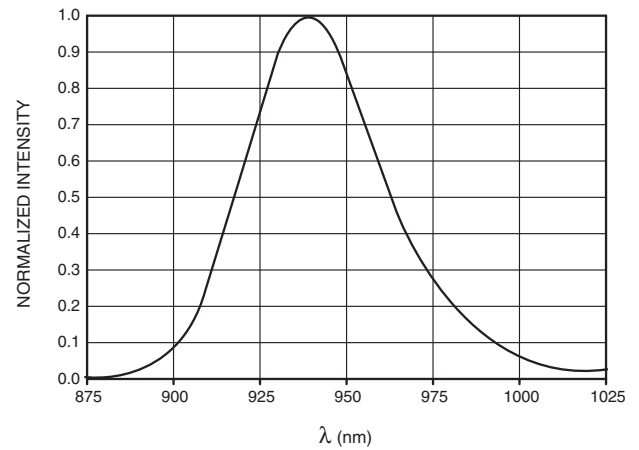
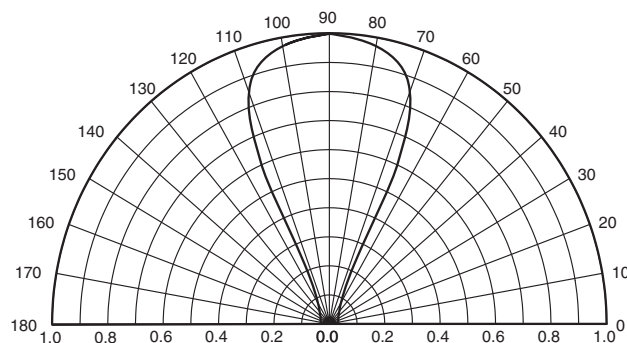


Fig. 5 Radiation Diagram



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